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(54) Title: VARIABLE FILM DOPANT CONCENTRATIONS FOR LATERAL ETCH RATE CONTROL IN REDUCED TEMPERATURE ETCHING

(57) Abstract: One disclosed example provides a method of performing cryoetching. The method comprises cooling a substrate in a processing chamber, while cooling the substrate, etching through a first film portion comprising a film material with a first dopant profile, and while cooling the substrate, etching at least partially through a second film portion comprising the film material with a second dopant profile different than the first dopant profile. The first dopant profile causes a different lateral etch rate of the film material than the second dopant profile.

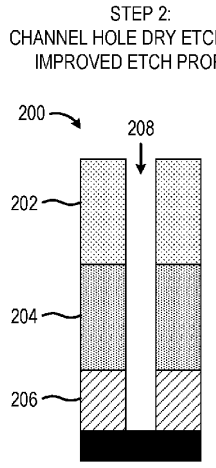

FIG. 2B

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